TOSHIBA Field Effect Transistor Silicon N·P Channel MOS Type

HN1L02FU

High Speed Switching Applications Analog Switch Applications

Q1, Q2 common

- 2.5V gate drive
- Low threshold voltage

Q1:
$$V_{th} = 0.5 \sim 1.5 V$$
 Q2: $V_{th} = -0.5 \sim -1.5 V$

- High speed
- Small package

Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	20	V
Gate-Source voltage	V _{GSS}	10	V
Drain current	I _D	50	mA

Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	-20	V
Gate-Source voltage	V _{GSS}	-7	V
Drain current	ID	-50	mA

Absolute Maximum Ratings (Q1, Q2 Common) (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain power dissipation	P _{D*}	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C

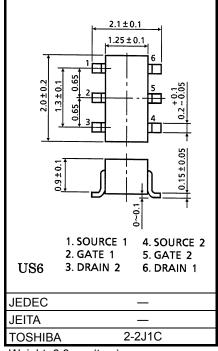
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate,

etc).

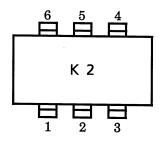
* Total rating

Unit in mm

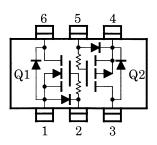


Weight: 6.8 mg (typ.)

Marking



Equivalent Circuit (top view)



Q1 Electrical Characteristics (Ta = 25°C)

Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = 10V, V _{DS} = 0	_	_	1	μΑ
Drain-Source breakdown voltage		V (BR) DSS	I _D = 100μA, V _{GS} = 0	20	_	_	V
Drain cut-off cur	rent	I _{DSS}	V _{DS} = 20V, V _{GS} = 0	_	_	1	μΑ
Gate threshold v	roltage	V _{th}	V _{DS} = 3V, I _D = 0.1mA	0.5	_	1.5	V
Forward transfer	admittance	Y _{fs}	V _{DS} = 3V, I _D = 10mA	20	_	_	mS
Drain-Source ON resistance		R _{DS} (ON)	I _D = 10mA, V _{GS} = 2.5V	_	20	40	Ω
Input capacitance		C _{iss}	V _{DS} = 3V, V _{GS} = 0, f = 1MHz	_	5.5	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 3V, V _{GS} = 0, f = 1MHz	_	1.6	_	pF
Output capacitance		C _{oss}	V _{DS} = 3V, V _{GS} = 0, f = 1MHz	_	6.5	_	pF
Switching time	Turn-on time	t _{on}	V _{DD} = 3V, I _D = 10mA, V _{GS} = 0~2.5V	_	0.14	_	μs
	Turn-off time	t _{off}	V _{DD} = 3V, I _D = 10mA, V _{GS} = 0~2.5V	_	0.14	_	μs

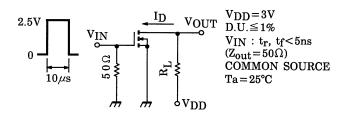
Q2 Electrical Characteristics (Ta = 25°C)

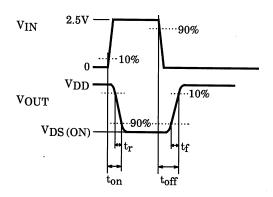
Chara	cteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = -7V, V _{DS} = 0	_	_	-1	μΑ
Drain-Source breakdown voltage		V _{(BR) DSS}	$I_D = -100\mu A, V_{GS} = 0$	-20	_	_	V
Drain cut-off cur	rent	I _{DSS}	$V_{DS} = -20V, V_{GS} = 0$	_	_	-1	μΑ
Gate threshold v	oltage	V _{th}	V _{DS} = -3V, I _D = -0.1mA	-0.5	_	-1.5	V
Forward transfer	admittance	Y _{fs}	$V_{DS} = -3V$, $I_{D} = -10mA$	15	_	_	mS
Drain-Source ON resistance		R _{DS} (ON)	$I_D = -10$ mA, $V_{GS} = -2.5$ V	1	20	40	Ω
Input capacitance		C _{iss}	$V_{DS} = -3V, V_{GS} = 0,$ f = 1MHz	-	10.4	-	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = -3V, V_{GS} = 0,$ f = 1MHz	_	2.8	_	pF
Output capacitance		C _{oss}	$V_{DS} = -3V, V_{GS} = 0,$ f = 1MHz	_	8.4	_	pF
Switching time	Turn-on time	t _{on}	V _{DD} = -3V, I _D = -10mA, V _{GS} = 0~-2.5V		0.15		μs
	Turn-off time	t _{off}	V _{DD} = -3V, I _D = -10mA, V _{GS} = 0~-2.5V	-	0.13	-	μs

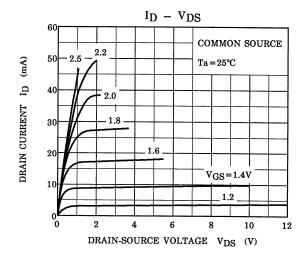
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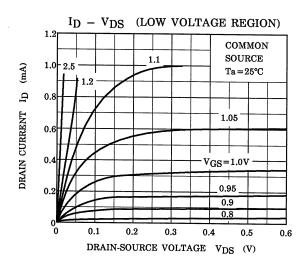
Q1 (Nch MOS FET)

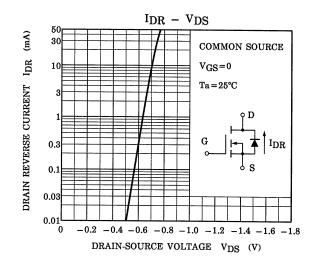
Switching Time Test Circuit

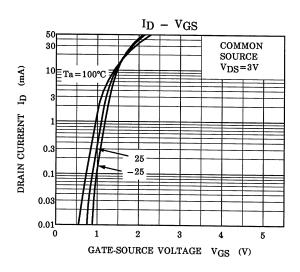




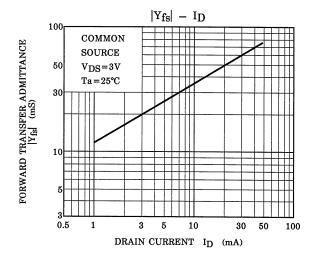


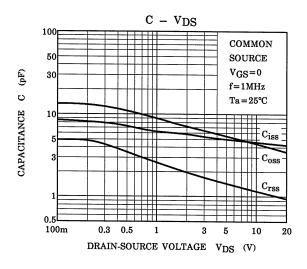


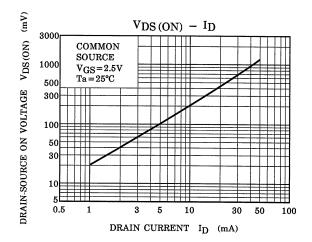


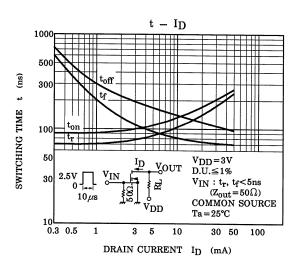


Q1 (Nch MOS FET)



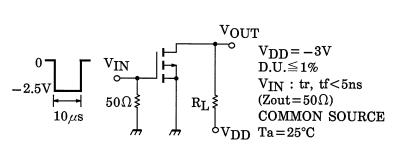


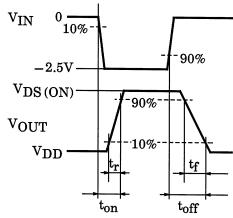


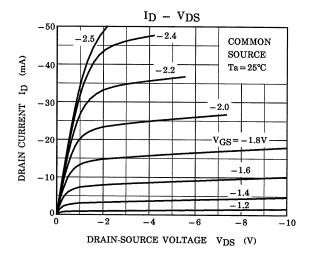


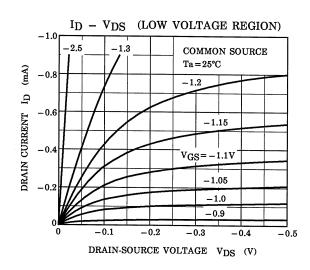
Q2 (Pch MOS FET)

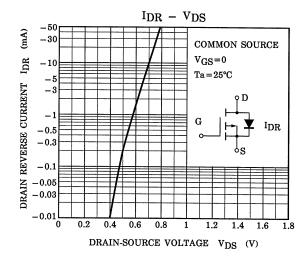
Switching Time Test Circuit

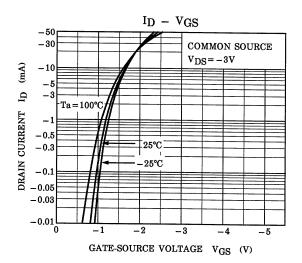




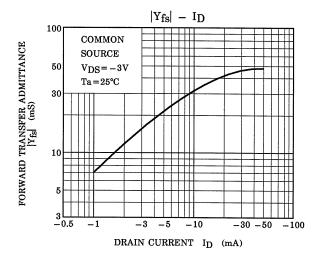


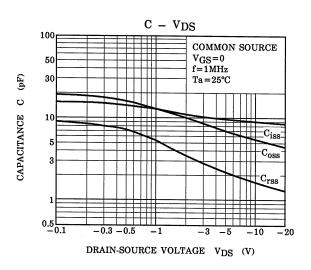


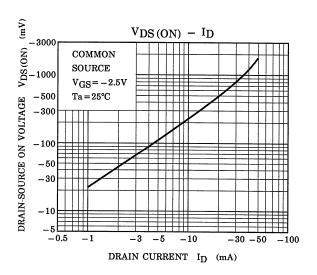


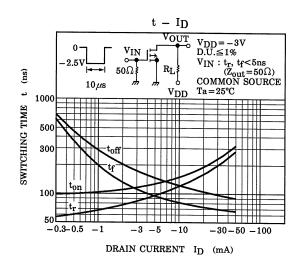


Q2 (Pch MOS FET)

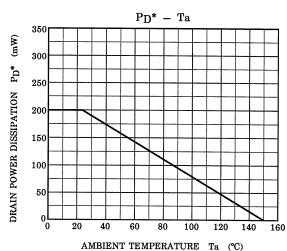








(Q1, Q2 common)



* : Total Rating

6

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